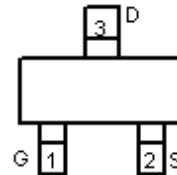


## P-Channel Enhancement Mode Power MOSFET

### Description

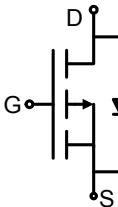
The SL2P03F uses advanced trench technology to provide excellent  $R_{DS(ON)}$ . This device is suitable for use as a load switch or in PWM applications.



### General Features

- $V_{DS} = -30V, I_D = -2.0A$
- $R_{DS(ON)} < 130m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} < 180m\Omega @ V_{GS}=-4.5V$

- High power and current handing capability
- Lead free product is acquired
- Surface mount package



Schematic diagram

### Application

- PWM applications
- Load switch
- Power management

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-2.0	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	-10	A
Maximum Power Dissipation	$P_D$	1.0	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	125	°C/W
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### Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

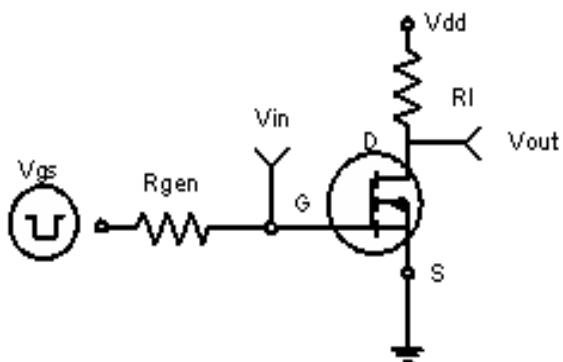
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-33	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	$\mu A$

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250µA	-1	-1.6	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.0A	-	72	130	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.5A	-	110	180	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A		2	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz	-	226	-	PF
Output Capacitance	C <sub>oss</sub>		-	47	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	28	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, R <sub>L</sub> =15Ω V <sub>GS</sub> =-10V, R <sub>GEN</sub> =6Ω	-	9	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	9	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	18	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	6	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-2.0A, V <sub>GS</sub> =-10V	-	8.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.5	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>s</sub> =-2.0A	-	-	-1.2	V

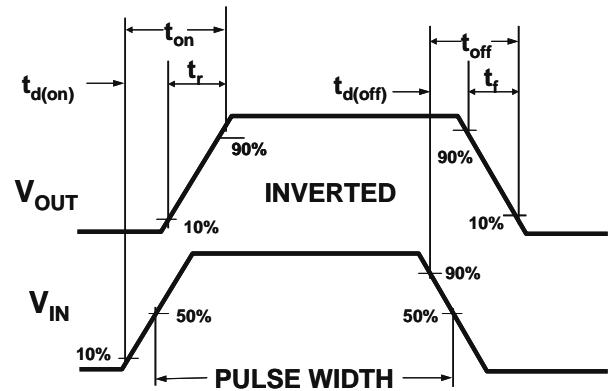
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

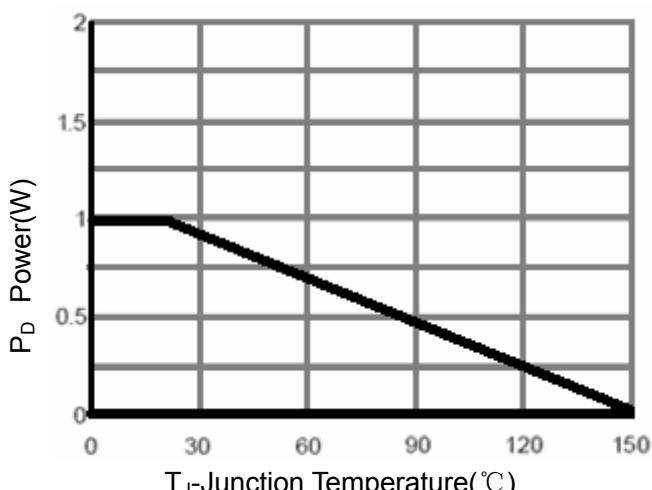
### Typical Electrical and Thermal Characteristics



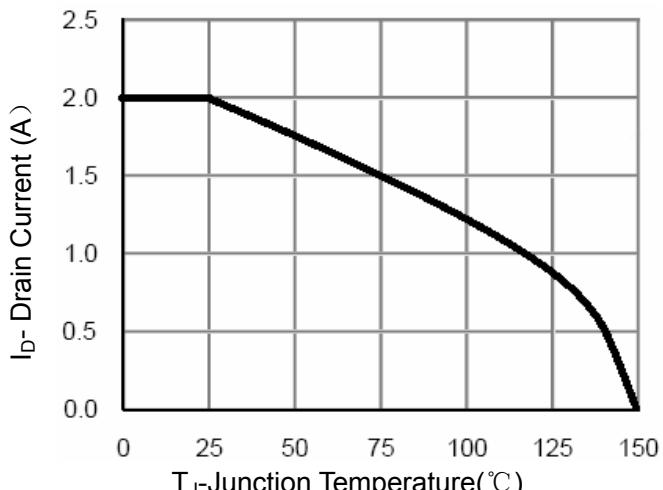
**Figure 1:Switching Test Circuit**



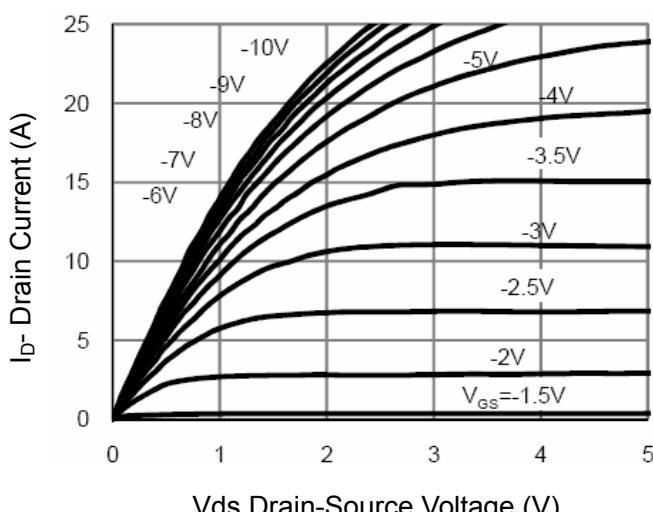
**Figure 2:Switching Waveforms**



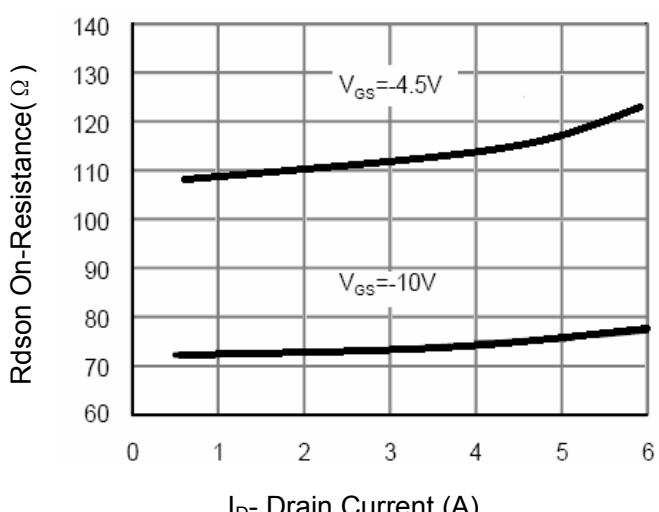
**Figure 3 Power Dissipation**



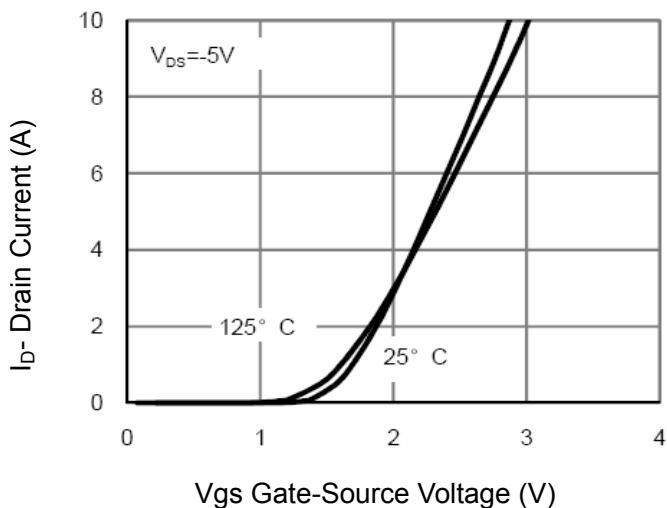
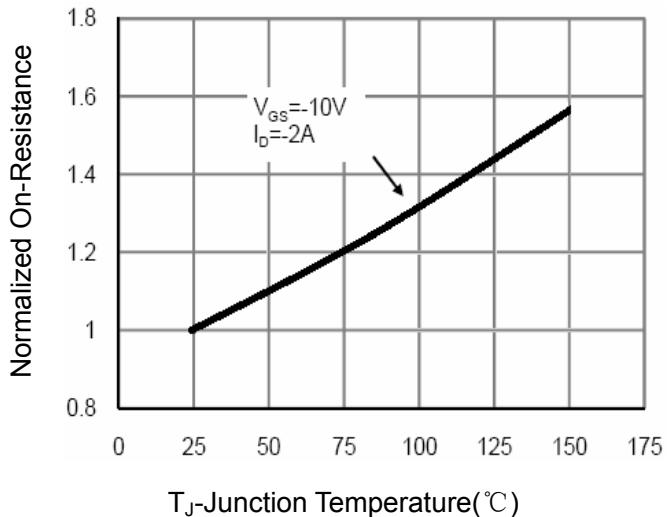
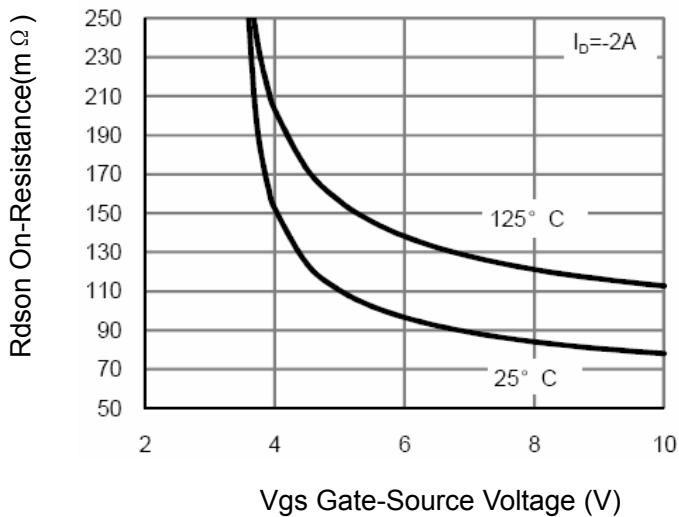
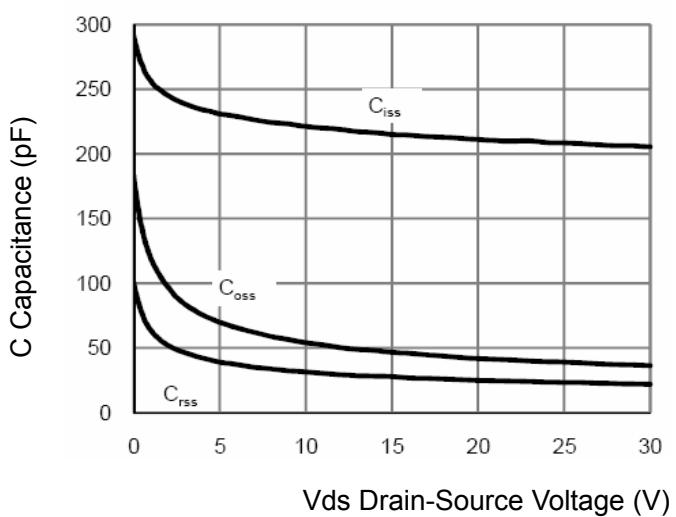
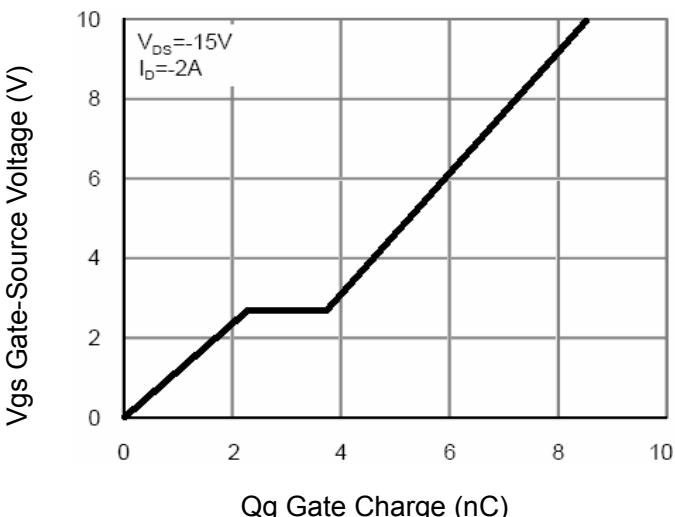
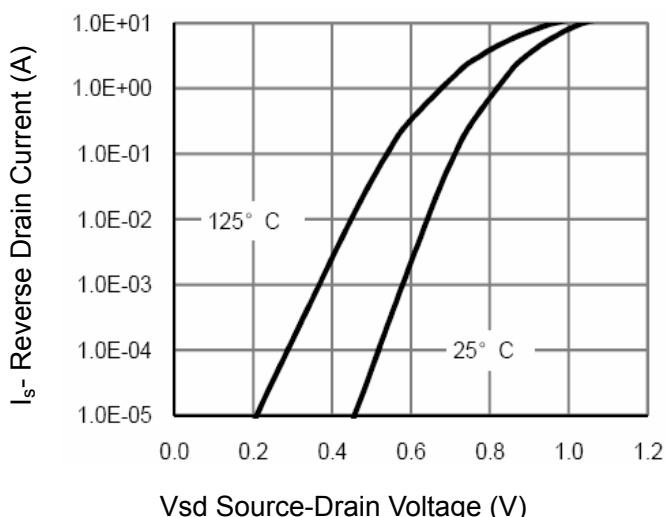
**Figure 4 Drain Current**



**Figure 5 Output Characteristics**



**Figure 6 Drain-Source On-Resistance**

**Figure 7 Transfer Characteristics****Figure 8 Drain-Source On-Resistance****Figure 9  $R_{DS(on)}$  vs  $V_{GS}$** **Figure 10 Capacitance vs  $V_{DS}$** **Figure 11 Gate Charge****Figure 12 Source- Drain Diode Forward**

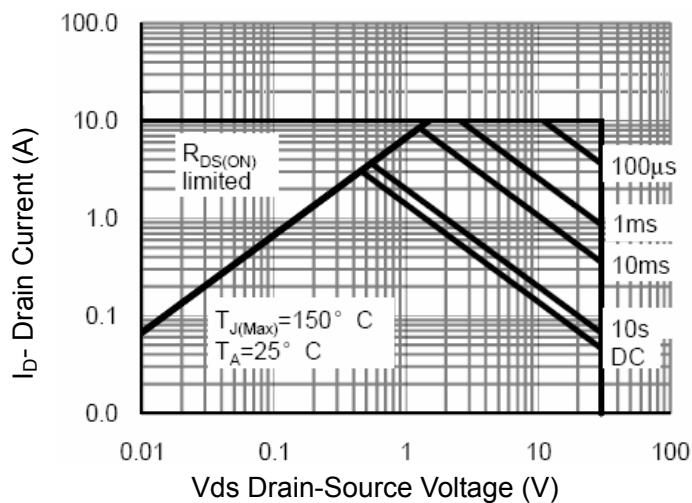


Figure 13 Safe Operation Area

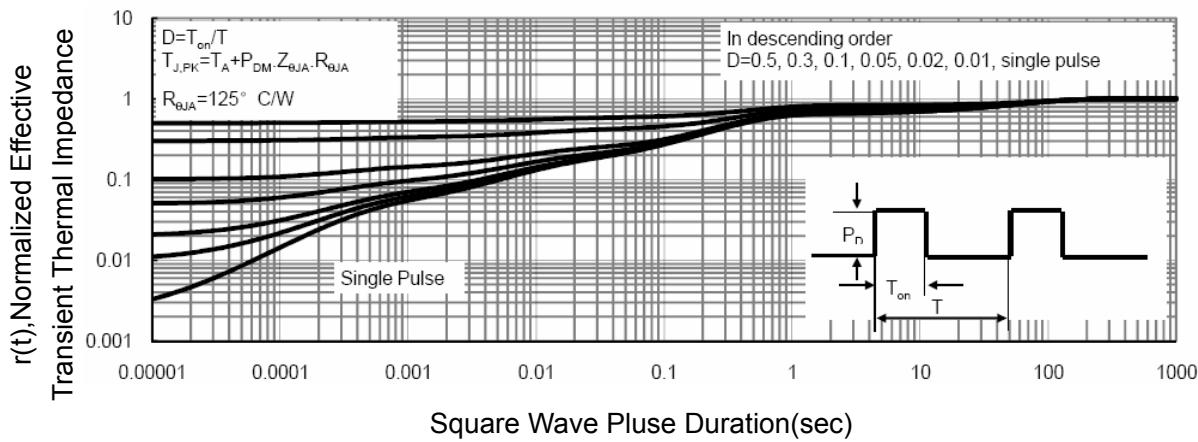
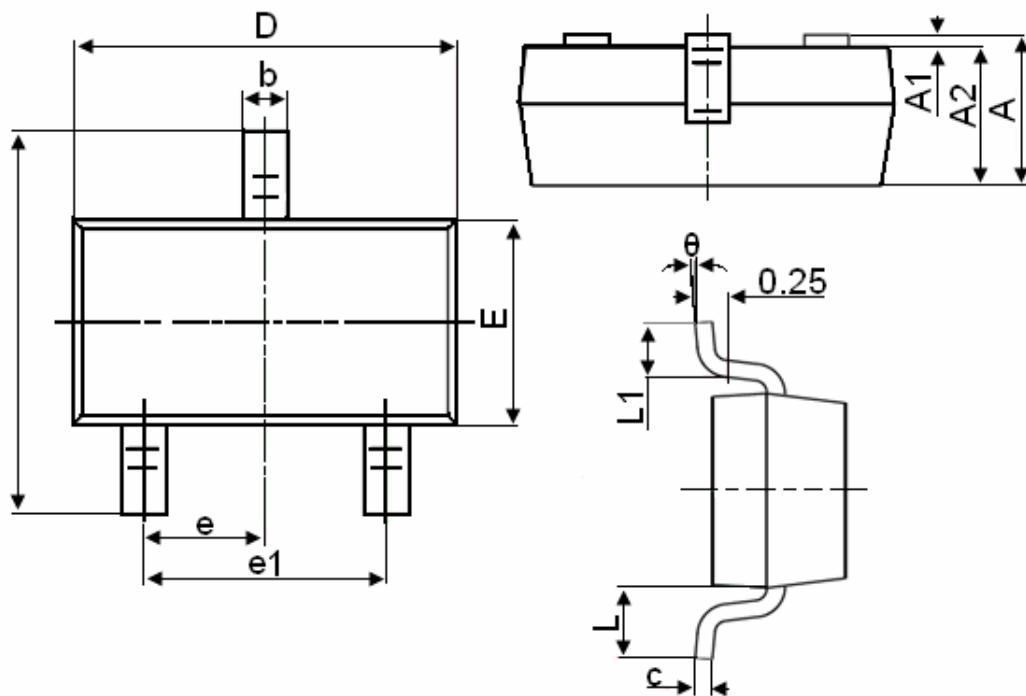


Figure 14 Normalized Maximum Transient Thermal Impedance

## SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

## Notes

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.